





300V NPN MEDIUM POWER TRANSISTOR IN SOT223

Features

- BV_{CEO} > 300V
- I_C = 3.5A High Continuous Collector Current
- I_{CM} = 5A Peak Pulse Current
- Very Low Saturation Voltage V_{CE(sat)} < 155mV @ 1A
- R_{CE(sat)} = 87mΩ for a Low Equivalent On-Resistance
- h_{FE} Specified Up to 3A for a High Gain Hold Up
- Complementary PNP Type: FZT957
- Lead-Free Finish; RoHS compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

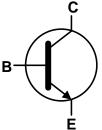
Mechanical Data

- Case: SOT223
- Case Material: Molded Plastic. "Green" Molding Compound.
 UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208@3
- Weight: 0.112 grams (Approximate)

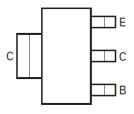




Top View



Device Symbol



Top View Pin-Out

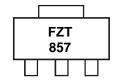
Ordering Information (Notes 4 & 5)

Product	Compliance	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
FZT857TA	AEC-Q101	FZT857	7	12	1,000
FZT857QTA	Automotive	FZT857	7	12	1,000

Notes:

- 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Automotive, AEC-Q101 and standard products are electrically and thermally the same, except where specified. For more information, please refer to http://www.diodes.com/quality/product_compliance_definitions/.
- 5. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



FZT857 = Product Type Marking Code





Absolute Maximum Ratings (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	350	V
Collector-Emitter Voltage	V _{CEO}	300	V
Emitter-Base Voltage	V _{EBO}	7	V
Continuous Collector Current	Ic	3.5	Α
Peak Pulse Current	I _{CM}	5	А

Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Power Dissipation	(Note 6)		3.0 24	W	
Linear Derating Factor	(Note 7)	P _D	1.6 12.8	mW/°C	
Thermal Desistance Junction to Ambient	(Note 6)	$R_{ heta JA}$	42		
Thermal Resistance, Junction to Ambient	(Note 7)	$R_{ heta JA}$	78	°C/W	
Thermal Resistance Junction to Lead (Note 8)		$R_{ heta JL}$	8.8	1	
Operating and Storage Temperature Range	T _{J,} T _{STG}	-55 to +150	°C		

ESD Ratings (Note 9)

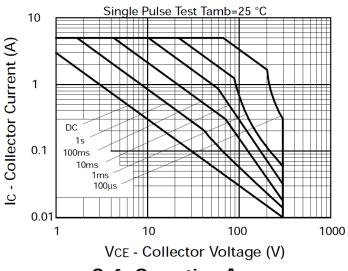
Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	8,000	V	3B
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

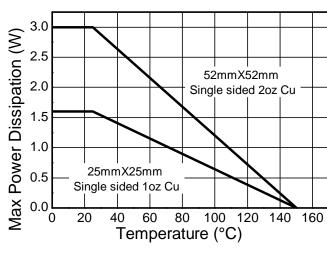
- 6. For a device mounted with the collector lead on 52mm x 52mm 2oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in steady-state.
- 7. Same as note (6), except the device is mounted on 25mm x 25mm 1oz copper.
- 8. Thermal resistance from junction to solder-point (at the end of the collector lead).

 9. Refer to JEDEC specification JESD22-A114 and JESD22-A115.



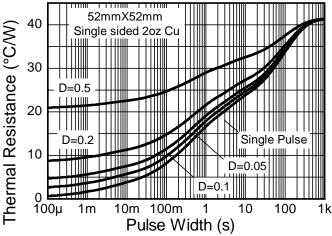
Thermal Characteristics and Derating Information

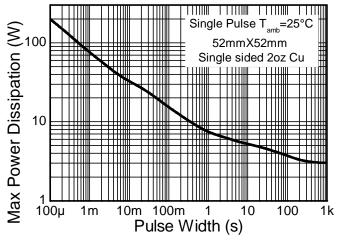




Safe Operating Area

Derating Curve





Transient Thermal Impedance

Pulse Power Dissipation





Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

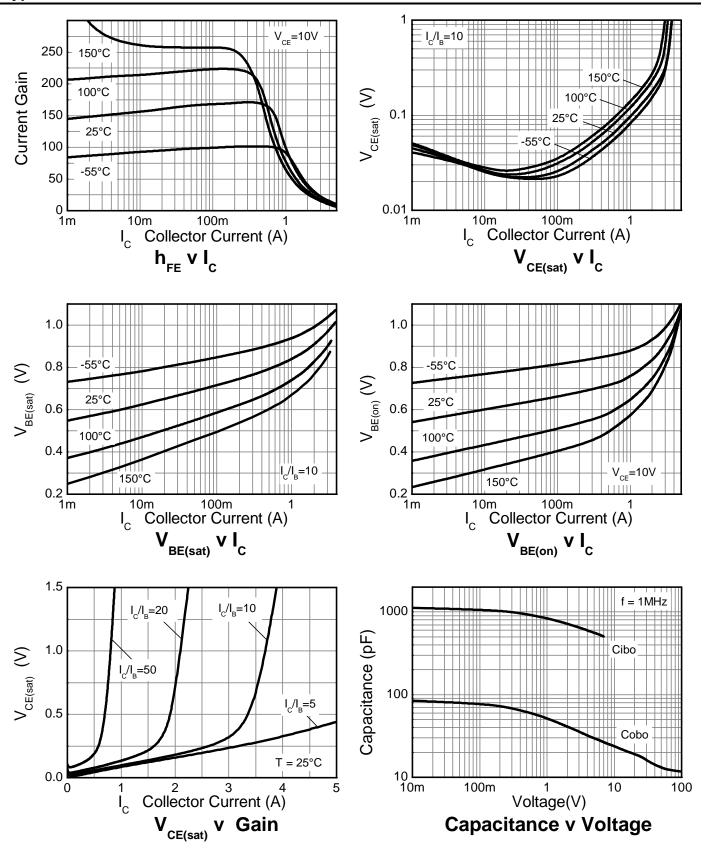
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV_{CBO}	350	475	_	V	$I_C = 100\mu A$
Collector-Emitter Breakdown Voltage	BV_{CER}	350	475	_	V	$I_C = 1\mu A, R_B \le 1k\Omega$
Collector-Emitter Breakdown Voltage (Note 10)	BV_{CEO}	300	350	_	V	$I_C = 1mA$
Emitter-Base Breakdown Voltage	BV_{EBO}	7	8	_	V	$I_E = 100\mu A$
Collector Cut-off Current	I _{CBO}	_ _	<1 -	50 1	nΑ μΑ	V _{CB} = 300V V _{CB} = 300V, T _A = +100°C
Collector Cut-off Current	I _{CER}	- -	<1 -	50 1	nΑ μΑ	$V_{CB} = 300V, R_B \le 1k\Omega$ $V_{CB} = 300V, T_A = +100$ °C
Emitter Cut-off Current	I _{EBO}	_	<1	10	nA	V _{EB} = 6V
		100	200	_		$I_C = 10 \text{mA}, V_{CE} = 5 \text{V}$
DC Current Gain (Note 10)	1.	100	200	300		$I_C = 500mA, V_{CE} = 10V$
DC Current Gain (Note 10)	h _{FE}	15	25	_	_	$I_C = 2A$, $V_{CE} = 10V$
		_	15	_		$I_C = 3A, V_{CE} = 10V$
		_	59	100		$I_C = 500mA$, $I_B = 50mA$
Collector-Emitter Saturation Voltage (Note 10)	V	_	95	155	mV	$I_C = 1A$, $I_B = 100mA$
Collector-Emilier Saturation voltage (Note 10)	V _{CE(sat)}	_	180	230	IIIV	$I_C = 2A$, $I_B = 200mA$
		_	300	345		$I_C = 3.5A$, $I_B = 600mA$
Base-Emitter Saturation Voltage (Note 10)	$V_{BE(sat)}$	_	1020	1250	mV	$I_C = 3.5A$, $I_B = 600mA$
Base-Emitter Turn-On Voltage (Note 10)	$V_{BE(on)}$	_	940	1120	mV	$I_C = 3.5A$, $V_{CE} = 10V$
Current Gain-Bandwidth Product (Note 10)	f _T	-	80	_	MHz	$I_C = 100 \text{mA}, V_{CE} = 10 \text{V},$ f = 50MHz
Output Capacitance (Note 10)	C_obo	-	21	_	pF	$V_{CB} = 20V$, $f = 1MHz$
Switching Times	t _{on}	_	100	_	ne	$I_C = 250 \text{mA}, V_{CC} = 50 \text{V},$
Switching filles	t _{off}	-	5300	_	ns	$I_{B1} = -I_{B2} = 25mA$

Note:

10. Measured under pulsed conditions. Pulse width ≤ 300µs. Duty cycle ≤ 2%



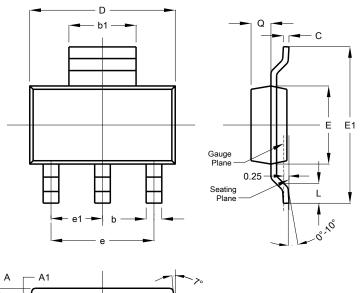
Typical Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)



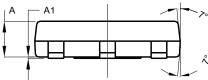


Package Outline Dimensions

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.

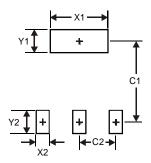


SOT223					
Dim	Min	Max	Тур		
Α	1.55	1.65	1.60		
A1	0.010	0.15	0.05		
b	0.60	0.80	0.70		
b1	2.90	3.10	3.00		
С	0.20	0.30	0.25		
D	6.45	6.55	6.50		
E	3.45	3.55	3.50		
E1	6.90	7.10	7.00		
е	-	-	4.60		
e1	-	-	2.30		
L	0.85	1.05	0.95		
Q	0.84	0.94	0.89		
All Dimensions in mm					



Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
X1	3.3
X2	1.2
Y1	1.6
Y2	1.6
C1	6.4
C2	2.3

Note: For high voltage applications, the appropriate industry sector guidelines should be considered with regards to creepage and clearance distances between device terminals and PCB tracking.





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